

Amendments to the Claims

Listing of Claims:

1. (Currently Amended) A method of creating a horizontal tip feature in a layer of tip material, comprising:
using an etch process to create an etch feature in the layer of tip material, the etch feature having horizontal areas and a substantially vertical sidewall, and the etch process having a slower etch rate near the substantially vertical sidewall than near the horizontal area; and
stopping the etch process in order to form a portion of the substantially vertical sidewall and a horizontal tip feature adjacent to the portion of the substantially vertical sidewall.
2. (Original) A method according to claim 1, further comprising:
monitoring the progress of the etch process.
3. (Original) A method according to claim 1, further comprising:
depositing the layer of tip material on a substrate material, the substrate material being different than the tip material.
4. (Original) A method according to claim 3, further comprising:
selecting an etch process that is selective to the tip material relative to the substrate material.
5. (Original) A method according to claim 1, further comprising:
varying a rate of polymer generation in order to control the slower etch rate of the etch process.

6. (Original) A method according to claim 1, further comprising:
determining the size of the horizontal tip feature to be created before using the etch process.
7. (Original) A method according to claim 1, further comprising:
controlling the profile of the substantially vertical sidewall.
8. (Original) A method according to claim 1, further comprising:
filling the etch feature with a lens material in order to form a lens having a shape determined by the shape of the etch feature.
9. (Original) A method according to claim 1, further comprising:
positioning a photo-sensitive device adjacent the layer of tip material such that the horizontal tip feature serves as an aperture for the photosensitive device.
10. (Original) A method according to claim 1, further comprising:
placing a photoresist mask over the layer of tip material, the photoresist mask acting as a mask for the etch process.
11. (Original) A method according to claim 10, wherein:
stopping the etch process causes the etch feature to have a critical dimension due to the horizontal tip feature that is less than the minimum dimension of the photoresist mask.
12. (Original) A method according to claim 1, wherein:
using an etch process includes using a reactive ion etch process.

13-20 (Cancelled)